ABSTRACT

Semiconductor device and manufacturing method thereof.

A semiconductor device 1000 comprises an electrically insulating film 10 having a device hole 12; lead groups 30A to 30D, each consisting of a large number of leads 30 arranged in a predetermined pattern, in a plurality of lead formation regions 100 to 400 on the surface of the film 10; an integrated circuit chip 20 positioned within the device hole 12 and with electrodes 22 connected to inner lead portions of the leads 30; and a resin sealing portion 50 that seals in at least the integrated circuit chip 20, the film 10, and the lead groups 30A to 30D.

The film 10 comprises a first group of aperture portions 14 consisting of aperture portions 14a to 14d provided in regions 500 to 800 outside the lead formation regions and a second group of aperture portions 16 consisting of a plurality of aperture portions 16a to 16e provided in the lead formation regions 100 to 400.

Fig. 1.